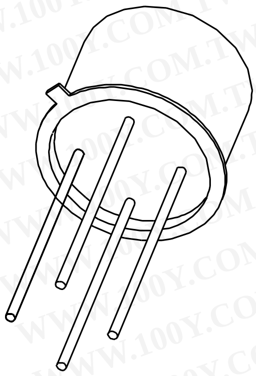
DISCRETE SEMICONDUCTORS

DATA SHEET



BRY39
Programmable unijunction transistor/ Silicon controlled switch

Product specification
Supersedes data of September 1994
File under Discrete Semiconductors, SC04

1997 Jul 24

Programmable unijunction transistor/ Silicon controlled switch

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FEATURES

- Silicon controlled switch
- Programmable unijunction transistor.

APPLICATIONS

- Switching applications such as:
  - Motor control
  - Oscillators
  - Relay replacement
  - Timers
  - Pulse shapers, etc.

DESCRIPTION

Silicon planar PNPN switch or trigger device in a TO-72 metal package.
It is an integrated PNP/NPN transistor pair with all electrodes accessible.

PINNING

PIN	DESCRIPTION
1	cathode
2	cathode gate
3	anode gate (connected to case)
4	anode

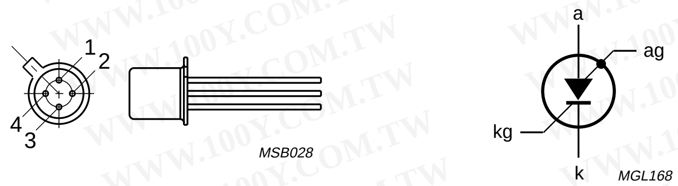

Fig.1 Simplified outline (TO-72) and symbol.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT
Silicon controlled switch				
PNP TRANSISTOR				
V_{EBO}	emitter-base voltage	open collector	–70	V
NPN TRANSISTOR				
V_{CBO}	collector-base voltage	open emitter	70	V
I_{ERM}	repetitive peak emitter current		–2.5	A
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C	275	mW
T_j	junction temperature		150	°C
V_{AK}	forward on-state voltage	$I_A = 50$ mA; $I_{AG} = 0$; $R_{KG\text{-}K} = 10$ kΩ	1.4	V
I_H	holding current	$I_{AG} = 10$ mA; $V_{BB} = -2$ V; $R_{KG\text{-}K} = 10$ kΩ	1	mA
t_{on}	turn-on time		0.25	µs
t_{off}	turn-off time		15	µs
Programmable unijunction transistor				
V_{GA}	gate-anode voltage		70	V
I_A	anode current (DC)	$T_{amb} \leq 25$ °C	175	mA
T_j	junction temperature		150	°C
I_p	peak point current	$V_S = 10$ V; $R_G = 10$ kΩ	0.2	µA

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C	–	275	mW
T_{stg}	storage temperature		–65	+200	°C
T_j	junction temperature		–	150	°C
T_{amb}	operating ambient temperature		–65	+150	°C
Silicon controlled switch					
V_{CBO}	collector-base voltage	open emitter			
	PNP		–	–70	V
	NPN		–	70	V
V_{CER}	collector-emitter voltage	R_{BE} = 10 kΩ			
	PNP		–	–	V
	NPN		–	70	V
V_{CEO}	collector-emitter voltage	open base			
	PNP		–	–70	V
	NPN		–	–	V
V_{EBO}	emitter-base voltage	open collector			
	PNP		–	–70	V
	NPN		–	5	V
I_C	collector current (DC)	note 1			
	PNP		–	–	
	NPN		–	175	mA
I_{CM}	peak collector current	note 2			
	PNP		–	–	
	NPN		–	175	mA
I_E	emitter current (DC)				
	PNP		–	175	mA
	NPN		–	–175	mA
I_{ERM}	repetitive peak emitter current	t_p = 10 µs; δ = 0.01			
	PNP		–	2.5	A
	NPN		–	–2.5	A
Programmable unijunction transistor					
V_{GA}	gate-anode voltage		–	70	V
I_A	anode current (AV)	$T_{amb} \leq 25$ °C	–	175	mA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{ARM}	repetitive peak anode current	t_p = 10 µs; δ = 0.01	–	2.5	A
I_{ASM}	non-repetitive peak anode current	t_p = 10 µs; T_j = 150 °C	–	3	A
dI_A/dt	rate of rise of anode current	I_A ≤ 2.5 A	–	20	A/µs

Notes

1. Provided the I_E rating is not exceeded.
2. During switching on, the device can withstand the discharge of a capacitor of a maximum value of 500 pF. This capacitor is charged when the transistor is in cut-off condition, with a collector supply voltage of 160 V and a series resistance of 100 kΩ.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	in free air	450	K/W

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Silicon controlled switch					
INDIVIDUAL PNP TRANSISTOR					
I_{CEO}	collector cut-off current	I_B = 0; V_{CE} = –70 V; T_j = 150 °C	–	–10	µA
I_{EBO}	emitter cut-off current	I_C = 0; V_{EB} = –70 V; T_j = 150 °C	–	–10	µA
h_{FE}	DC current gain	I_E = 1 mA; V_{CE} = –5 V	3	15	
INDIVIDUAL NPN TRANSISTOR					
I_{CER}	collector cut-off current	V_{CE} = 70 V; R_{BE} = 10 kΩ	–	100	nA
		V_{CE} = 70 V; R_{BE} = 10 kΩ; T_j = 150 °C	–	10	µA
I_{EBO}	emitter cut-off current	I_C = 0; V_{EB} = 5 V; T_j = 150 °C	–	10	µA
V_{CEsat}	collector-emitter saturation voltage	I_C = 10 mA; I_B = 1 mA	–	0.5	V
V_{BEsat}	base-emitter saturation voltage	I_C = 10 mA; I_B = 1 mA	–	0.9	V
h_{FE}	DC current gain	I_C = 10 mA; V_{CE} = 2 V	50	–	
C_c	collector capacitance	I_E = i_e = 0; V_{CB} = 20 V	–	5	pF
C_e	emitter capacitance	I_C = i_c = 0; V_{EB} = 1 V; f = 1 MHz	–	25	pF
f_T	transition frequency	I_C = 10 mA; V_{CE} = 2 V; f = 100 MHz	100	–	MHz
COMBINED DEVICE					
V_{AK}	forward on-state voltage	R_{KG-K} = 10 kΩ			
		I_A = 50 mA; I_{AG} = 0	–	1.4	V
		I_A = 50 mA; I_{AG} = 0; T_j = –55 °C	–	1.9	V
		I_A = 1 mA; I_{AG} = 10 mA	–	1.2	V
I_H	holding current	V_{BB} = –2 V; I_{AG} = 10 mA; R_{KG-K} = 10 kΩ; see Fig.14	–	1	mA

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SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
SWITCHING TIMES					
t_{on}	turn-on time	V_{KG-K} = –0.5 to 4.5 V; R_{KG-K} = 1 kΩ; see Figs 15 and 16	–	0.25	µs
		V_{KG-K} = –0.5 to 0.5 V; R_{KG-K} = 10 kΩ	–	1.5	µs
t_{off}	turn-off time	R_{KG-K} = 10 kΩ; see Figs 17 and 18	–	15	µs
Programmable unijunction transistor					
I_p	peak point current	V_S = 10 V; R_G = 10 kΩ; see Figs 3 and 8	–	0.2	µA
		V_S = 10 V; R_G = 100 kΩ; see Figs 3 and 8	–	0.06	µA
I_v	valley point current	V_S = 10 V; R_G = 10 kΩ; see Figs 3 and 8	–	2	µA
		V_S = 10 V; R_G = 100 kΩ; see Figs 3 and 8	–	1	µA
V_{offset}	offset voltage	typical curve; I_A = 0; for V_P and V_S see Fig.8	–	–	V
I_{GAO}	gate-anode leakage current	I_K = 0; V_{GA} = 70 V	–	10	nA
I_{GKS}	gate-cathode leakage current	V_{AK} = 0; V_{KG} = 70 V	–	100	nA
V_{AK}	anode-cathode voltage	I_A = 100 mA	–	1.4	V
V_{OM}	peak output voltage	V_{AA} = 20 V; C = 10 nF; see Figs 9 and 11	6	–	V
t_r	rise time	V_{AA} = 20 V; C = 10 nF; see Fig.11	–	80	ns

Explanation of symbols

For application of the BRY39 as a programmable unijunction transistor, only the anode gate is used. To simplify the symbols, the term gate instead of anode gate will be used (see Fig.2).

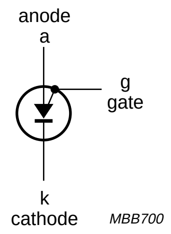

Fig.2 Programmable unijunction transistor explanation of symbols.

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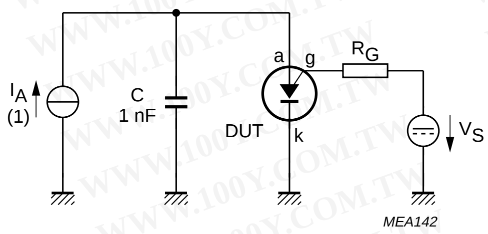

Fig.3 Programmable unijunction transistor test circuit for peak and valley points.

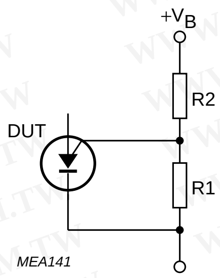

Fig.4 Programmable unijunction transistor with 'program' resistors R1 and R2.

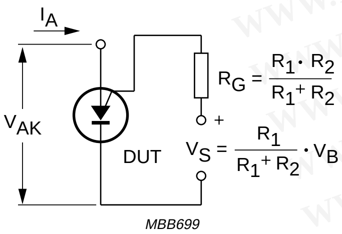

Fig.5 Programmable unijunction transistor equivalent test circuit for characteristics testing.

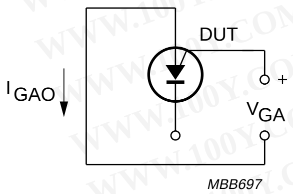

Fig.6 Programmable unijunction transistor equivalent test circuit for gate-anode leakage current.

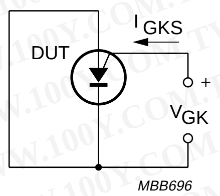

Fig.7 Programmable unijunction transistor equivalent test circuit for gate-cathode leakage current.

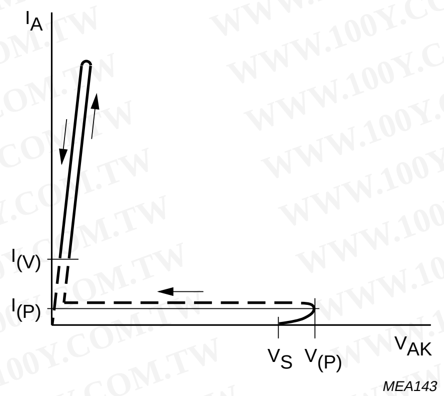

Fig.8 Programmable unijunction transistor offset voltage.

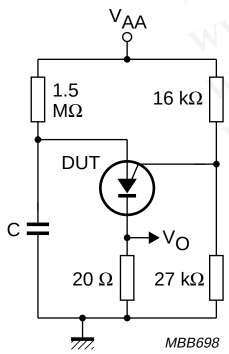

Fig.9 Programmable unijunction transistor test circuit for peak output voltage.

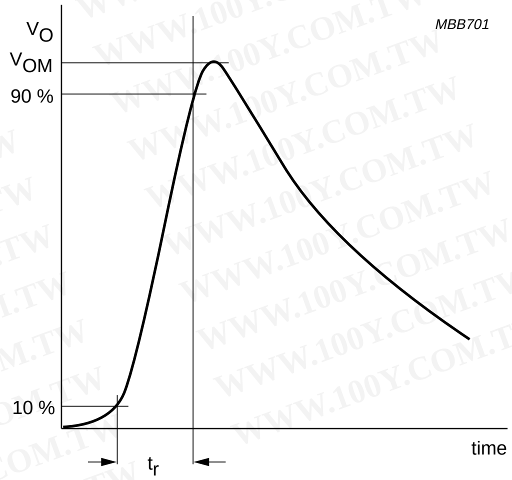

Fig.10 Programmable unijunction transistor peak output voltage.

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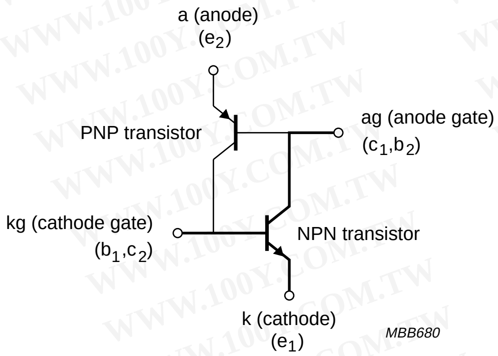

Fig.11 Silicon controlled switch two transistor equivalent circuit.

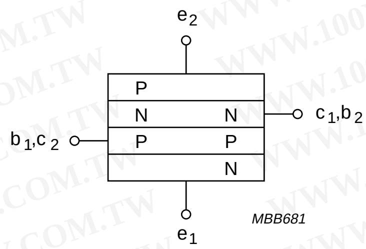

Fig.12 PNPN silicon controlled switch structure.

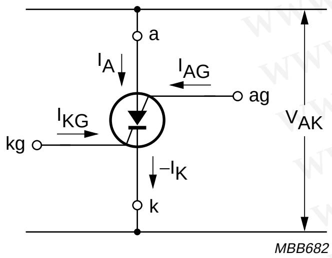

Fig.13 Silicon controlled switch symbol.

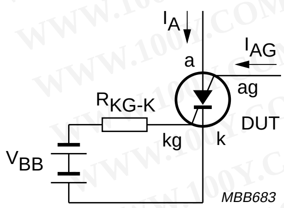

Fig.14 Silicon controlled switch equivalent test circuit for holding current.

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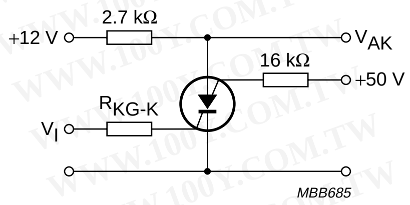

Fig.15 Silicon controlled switch test circuit for turn-on time.

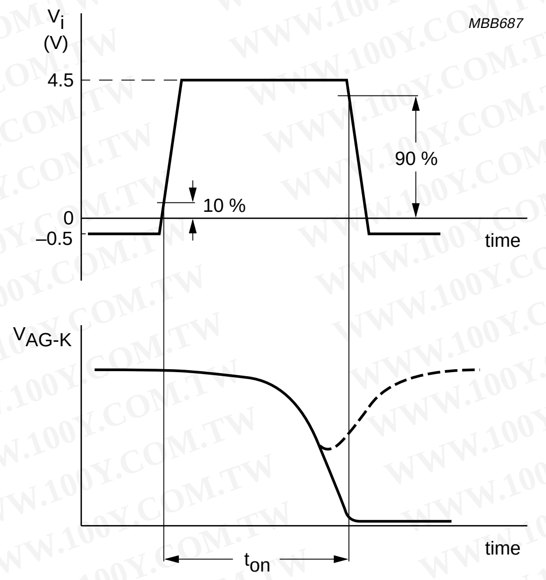

Fig.16 Silicon controlled switch pulse duration increased until dashed curve disappears.

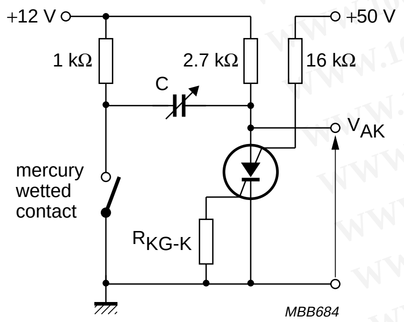

Fig.17 Silicon controlled switch test circuit for turn-on time.

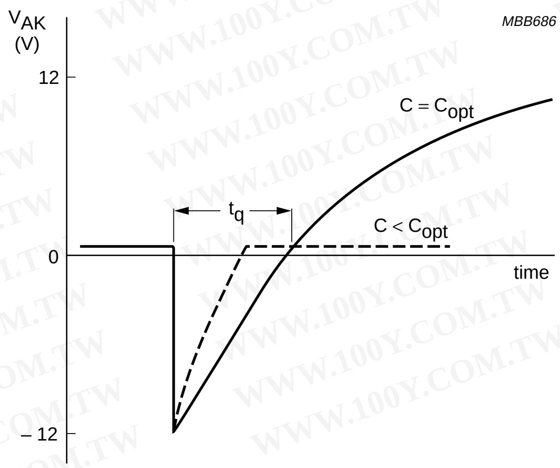

Fig.18 Silicon controlled switch capacitance increased until $C = C_{opt}$ dashed curve disappears.

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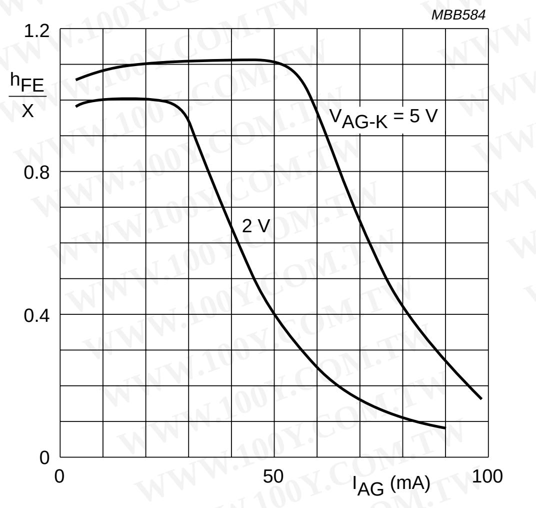
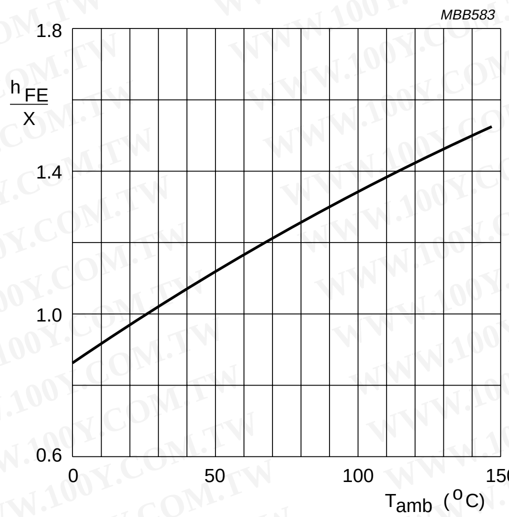


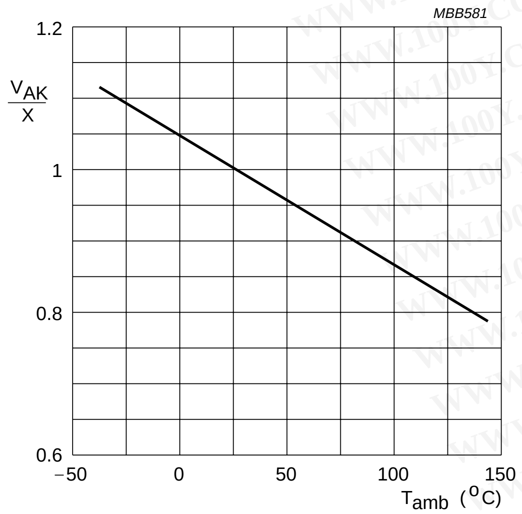
X = value of h_{FE} at I_C = 10 mA; $V_{AG\text{-}K}$ = 2 V; T_{amb} = 25 °C.

Fig.19 Silicon controlled switch normalized DC current gain as a function of anode gate current.



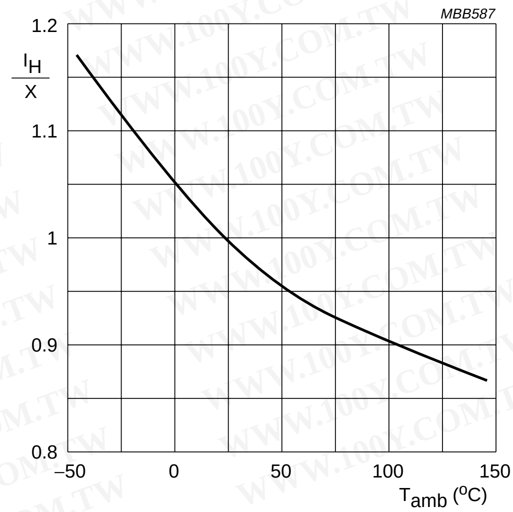
X = value of h_{FE} at I_{AG} = 10 mA; $V_{AG\text{-}K}$ = 2 V; T_{amb} = 25 °C.

Fig.20 Silicon controlled switch normalized DC current gain as a function of ambient temperature.



X = value of V_{AK} at I_A = 1 mA; I_{AG} = 10 mA; V_{BB} = −2 V; $R_{KG\text{-}K}$ = 10 kΩ; T_{amb} = 25 °C.

Fig.21 Silicon controlled switch normalized anode-cathode voltage as a function of ambient temperature.



X = value of I_H at I_{AG} = 10 mA; V_{BB} = −2 V; $R_{KG\text{-}K}$ = 10 kΩ; T_{amb} = 25 °C.

Fig.22 Silicon controlled switch normalized holding current as a function of ambient temperature.

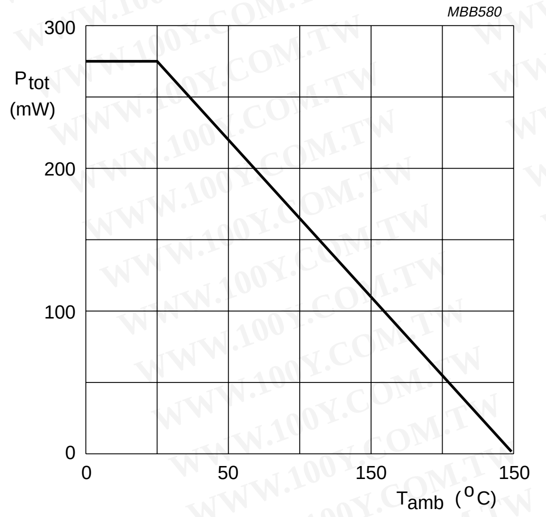


Fig.23 Silicon controlled switch power derating curve.

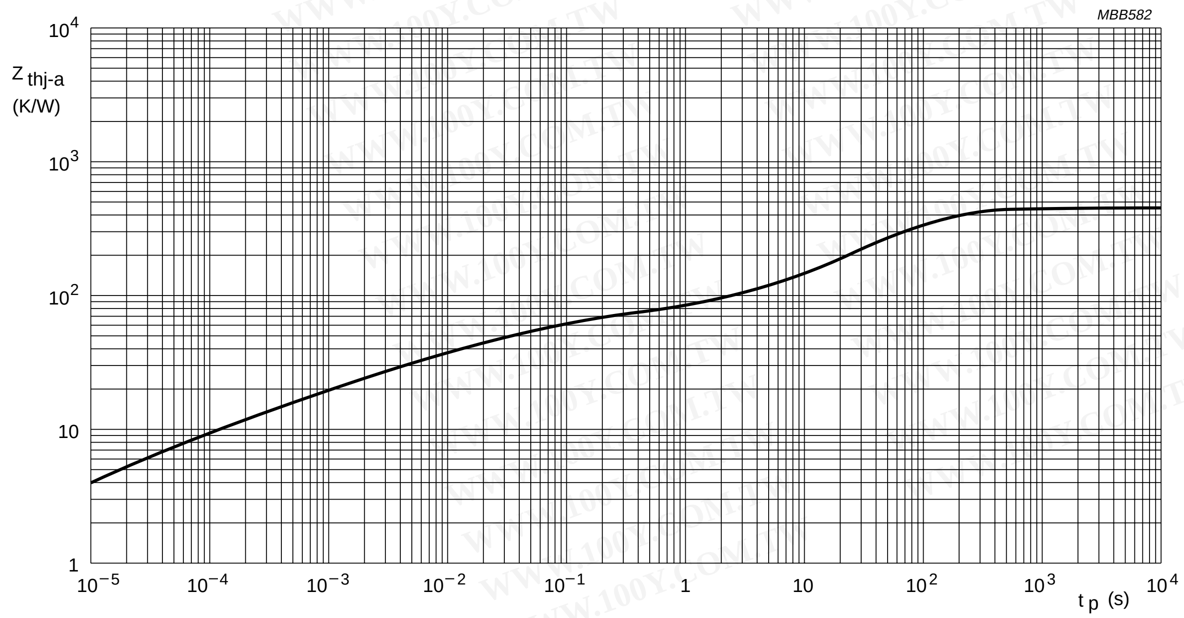
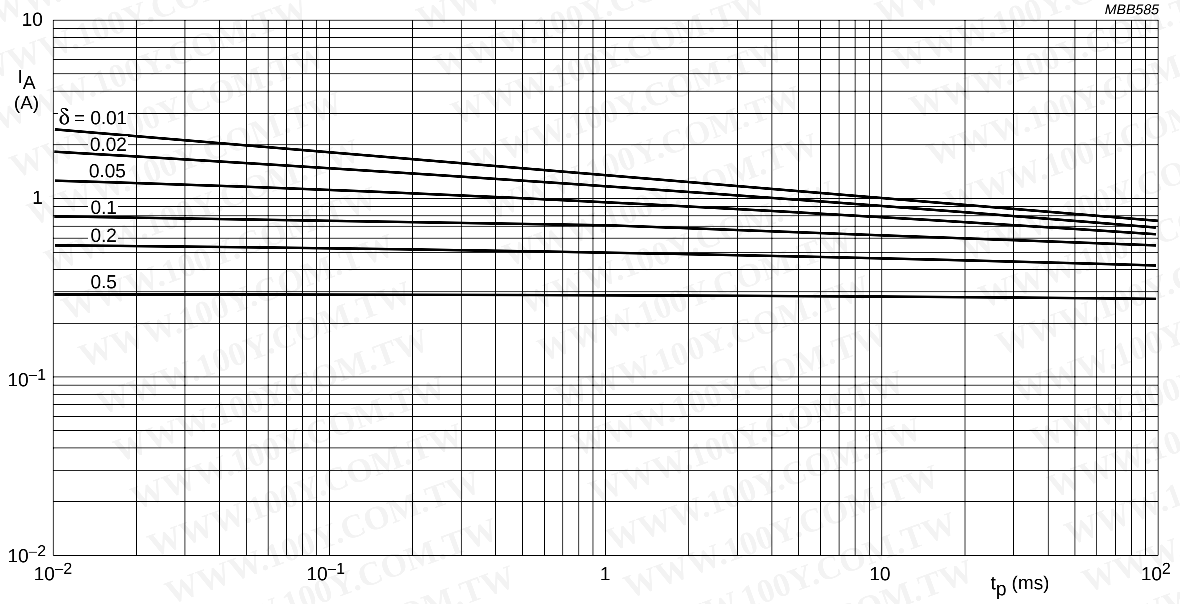
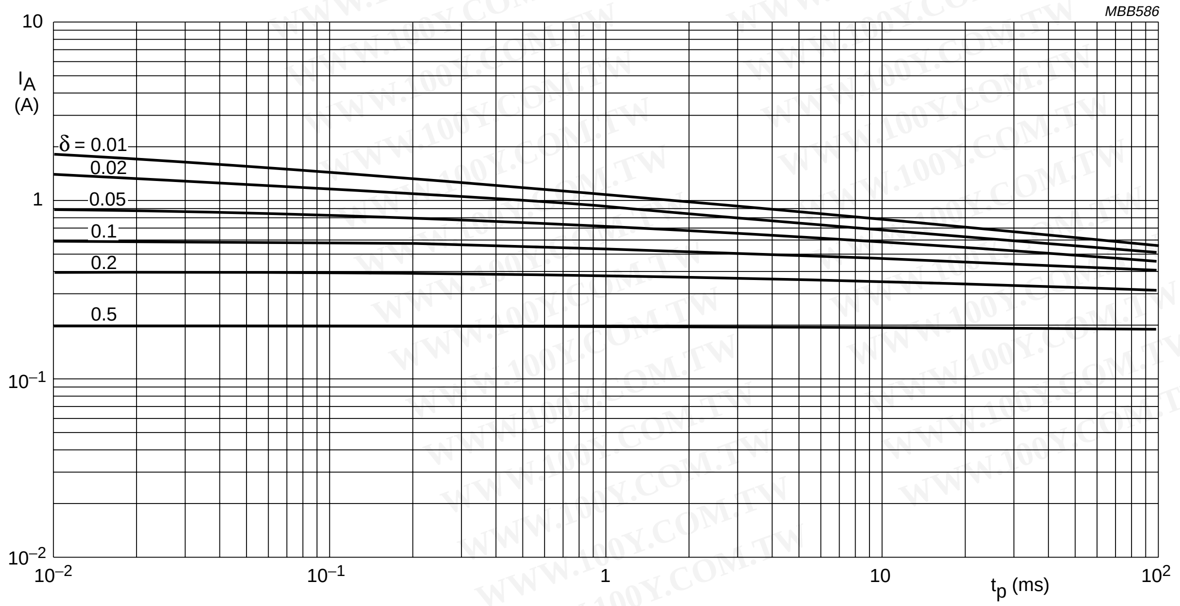


Fig.24 Silicon controlled switch thermal impedance as a function of pulse duration.



T_{amb} = 25 °C.

Fig.25 Silicon controlled switch anode current as a function of pulse duration.



T_{amb} = 70 °C.

Fig.26 Silicon controlled switch anode current as a function of pulse duration.

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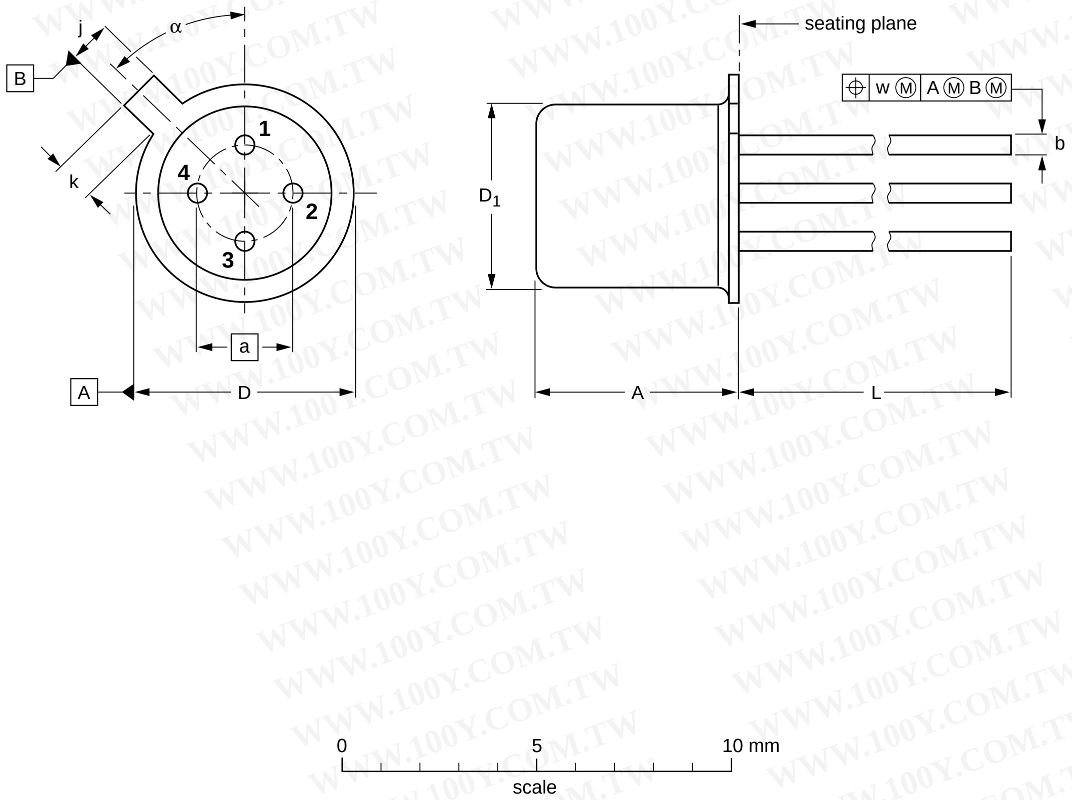
PACKAGE OUTLINE

Metal-can cylindrical single-ended package; 4 leads **SOT18/9**



DIMENSIONS (millimetre dimensions are derived from the original inch dimensions)

UNIT	A	a	b	D	D_1	j	k	L	w	α
mm	5.31 4.74	2.54	0.46 0.42	5.45 5.30	4.70 4.55	1.05 0.95	1.0 0.9	14.5 13.5	0.36	45°

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT18/9	B12/C7 type 3	TO-72				97-04-18

DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

LIFE SUPPORT APPLICATIONS

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